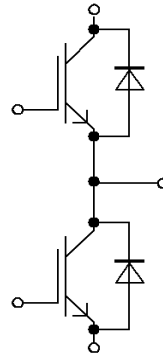


62mm C-Series 模块 采用第四代高速沟槽栅/场终止IGBT和HE型发射极控制二极管 和预涂导热介质  
 62mm C-Series module with fast Trench/Fieldstop IGBT4 and Emitter Controlled HE diode and pre-applied Thermal Interface Material



$V_{CES} = 1200V$   
 $I_{C\ nom} = 400A / I_{CRM} = 800A$

### 典型应用

- 大功率变流器
- 电机传动
- UPS系统
- 风力发电机

### Typical Applications

- High power converters
- Motor drives
- UPS systems
- Wind turbines

### 电气特性

- 提高工作结温  $T_{vj\ op}$
- 低开关损耗
- 低  $V_{CEsat}$
- 无与伦比的坚固性
- $V_{CEsat}$  带正温度系数

### Electrical Features

- Extended operating temperature  $T_{vj\ op}$
- Low switching losses
- Low  $V_{CEsat}$
- Unbeatable robustness
- $V_{CEsat}$  with positive temperature coefficient

### 机械特性

- 4 kV 交流 1分钟 绝缘
- 封装的 CTI > 400
- 高爬电距离和电气间隙
- 高功率密度
- 绝缘的基板
- 标准封装
- 预涂导热介质

### Mechanical Features

- 4 kV AC 1min insulation
- Package with CTI > 400
- High creepage and clearance distances
- High power density
- Isolated base plate
- Standard housing
- Pre-applied Thermal Interface Material

## Module Label Code

Barcode Code 128



DMX - Code



Content of the Code

Content of the Code	Digit
Module Serial Number	1 - 5
Module Material Number	6 - 11
Production Order Number	12 - 19
Datecode (Production Year)	20 - 21
Datecode (Production Week)	22 - 23

## IGBT, 逆变器 / IGBT, Inverter

## 最大额定值 / Maximum Rated Values

集电极 - 发射极电压 Collector-emitter voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{CES}$	1200	V
连续集电极直流电流 Continuous DC collector current	$T_H = 85^{\circ}\text{C}, T_{vj\max} = 175^{\circ}\text{C}$	$I_{C\text{nom}}$	400	A
集电极重复峰值电流 Repetitive peak collector current	$t_P = 1\text{ ms}$	$I_{CRM}$	800	A
栅极 - 发射极峰值电压 Gate-emitter peak voltage		$V_{GES}$	+/-20	V

## 特征值 / Characteristic Values

			min.	typ.	max.		
集电极 - 发射极饱和电压 Collector-emitter saturation voltage	$I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$ $I_C = 400\text{ A}, V_{GE} = 15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_{CE\text{sat}}$	1,65 1,90 1,95	2,05	V V V	
栅极阈值电压 Gate threshold voltage	$I_C = 17,0\text{ mA}, V_{CE} = V_{GE}, T_{vj} = 25^{\circ}\text{C}$		$V_{GEth}$	5,25	5,80	6,35	V
栅极电荷 Gate charge	$V_{GE} = -15\text{ V} \dots +15\text{ V}$		$Q_G$	3,60			$\mu\text{C}$
内部栅极电阻 Internal gate resistor	$T_{vj} = 25^{\circ}\text{C}$		$R_{Gint}$	1,9			$\Omega$
输入电容 Input capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{ies}$	28,0			nF
反向传输电容 Reverse transfer capacitance	$f = 1\text{ MHz}, T_{vj} = 25^{\circ}\text{C}, V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}$		$C_{res}$	1,10			nF
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE} = 1200\text{ V}, V_{GE} = 0\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{CES}$			5,0	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}, T_{vj} = 25^{\circ}\text{C}$		$I_{GES}$			400	nA
开通延迟时间(电感负载) Turn-on delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{don}$	0,14 0,15 0,16			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
上升时间(电感负载) Rise time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_r$	0,04 0,04 0,045			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
关断延迟时间(电感负载) Turn-off delay time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_{doff}$	0,40 0,46 0,48			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
下降时间(电感负载) Fall time, inductive load	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}$ $V_{GE} = \pm 15\text{ V}$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$t_f$	0,09 0,14 0,16			$\mu\text{s}$ $\mu\text{s}$ $\mu\text{s}$
开通损耗能量(每脉冲) Turn-on energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, di/dt = 9000\text{ A}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Gon} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{on}$	17,0 26,5 32,0			mJ mJ mJ
关断损耗能量(每脉冲) Turn-off energy loss per pulse	$I_C = 400\text{ A}, V_{CE} = 600\text{ V}, L_S = 30\text{ nH}$ $V_{GE} = \pm 15\text{ V}, du/dt = 4500\text{ V}/\mu\text{s} (T_{vj} = 150^{\circ}\text{C})$ $R_{Goff} = 1,0\ \Omega$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{off}$	23,0 35,5 38,0			mJ mJ mJ
短路数据 SC data	$V_{GE} \leq 15\text{ V}, V_{CC} = 800\text{ V}$ $V_{CEmax} = V_{CES} - L_{SCE} \cdot di/dt$ $t_P \leq 10\ \mu\text{s}, T_{vj} = 150^{\circ}\text{C}$		$I_{SC}$	1800			A
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个 IGBT / per IGBT valid with IFX pre-applied thermal interface material		$R_{thJH}$			0,0859	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{op}}$	-40		150	$^{\circ}\text{C}$

## 二极管, 逆变器 / Diode, Inverter

### 最大额定值 / Maximum Rated Values

反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj} = 25^{\circ}\text{C}$	$V_{RRM}$	1200	V
连续正向直流电流 Continuous DC forward current		$I_F$	400	A
正向重复峰值电流 Repetitive peak forward current	$t_P = 1\text{ ms}$	$I_{FRM}$	800	A
$I^2t$ -值 $I^2t$ - value	$V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 125^{\circ}\text{C}$ $V_R = 0\text{ V}, t_P = 10\text{ ms}, T_{vj} = 150^{\circ}\text{C}$	$I^2t$	34000 32000	$\text{A}^2\text{s}$ $\text{A}^2\text{s}$

### 特征值 / Characteristic Values

			min.	typ.	max.	
正向电压 Forward voltage	$I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$ $I_F = 400\text{ A}, V_{GE} = 0\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$V_F$	1,65 1,65 1,65	2,20	V V V
反向恢复峰值电流 Peak reverse recovery current	$I_F = 400\text{ A}, -di_F/dt = 9000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$I_{RM}$	435 490 500		A A A
恢复电荷 Recovered charge	$I_F = 400\text{ A}, -di_F/dt = 9000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$Q_r$	39,0 71,0 80,0		$\mu\text{C}$ $\mu\text{C}$ $\mu\text{C}$
反向恢复损耗 (每脉冲) Reverse recovery energy	$I_F = 400\text{ A}, -di_F/dt = 9000\text{ A}/\mu\text{s} (T_{vj}=150^{\circ}\text{C})$ $V_R = 600\text{ V}$ $V_{GE} = -15\text{ V}$	$T_{vj} = 25^{\circ}\text{C}$ $T_{vj} = 125^{\circ}\text{C}$ $T_{vj} = 150^{\circ}\text{C}$	$E_{rec}$	17,0 33,5 37,0		mJ mJ mJ
结 - 散热器热阻 Thermal resistance, junction to heatsink	每个二极管 / per diode valid with IFX pre-applied thermal interface material		$R_{thJH}$		0,151	K/W
在开关状态下温度 Temperature under switching conditions			$T_{vj\text{ op}}$	-40	150	$^{\circ}\text{C}$

### 模块 / Module

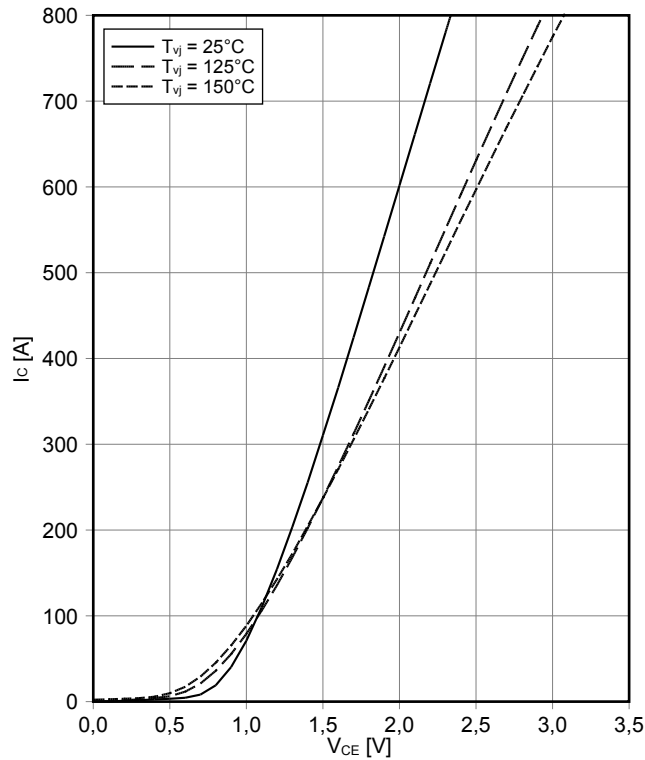
绝缘测试电压 Isolation test voltage	RMS, $f = 50\text{ Hz}, t = 1\text{ min.}$	$V_{ISOL}$	4,0	kV	
模块基板材料 Material of module baseplate			Cu		
内部绝缘 Internal isolation	基本绝缘 (class 1, IEC 61140) basic insulation (class 1, IEC 61140)		$\text{Al}_2\text{O}_3$		
爬电距离 Creepage distance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		29,0 23,0	mm	
电气间隙 Clearance	端子至散热器 / terminal to heatsink 端子至端子 / terminal to terminal		23,0 11,0	mm	
相对电痕指数 Comperative tracking index		CTI	> 400		
			min.	typ.	max.
杂散电感, 模块 Stray inductance module		$L_{sCE}$	20	nH	
模块引线电阻, 端子-芯片 Module lead resistance, terminals - chip	$T_H = 25^{\circ}\text{C}$ , 每个开关 / per switch	$R_{CC+EE'}$	0,70	m $\Omega$	
储存温度 Storage temperature		$T_{stg}$	-40	125	$^{\circ}\text{C}$
最高基板工作温度 Maximum baseplate operation temperature		$T_{BPmax}$		125	$^{\circ}\text{C}$
模块安装的安装扭矩 Mounting torque for modul mounting	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	3,00	6,00	Nm
端子联接扭矩 Terminal connection torque	螺丝 M6 根据相应的应用手册进行安装 Screw M6 - Mounting according to valid application note	M	2,5	5,0	Nm
重量 Weight		G	340	g	

Lagerung und Transport von Modulen mit TIM => siehe AN2012-07  
Storage and shipment of modules with TIM => see AN2012-07

输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

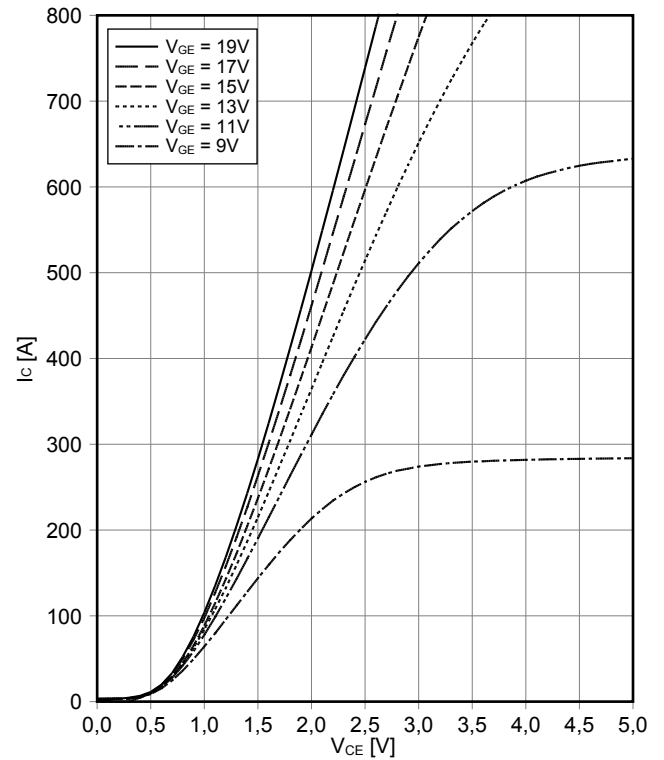
$I_C = f(V_{CE})$   
 $V_{GE} = 15\text{ V}$



输出特性 IGBT, 逆变器 (典型)

output characteristic IGBT, Inverter (typical)

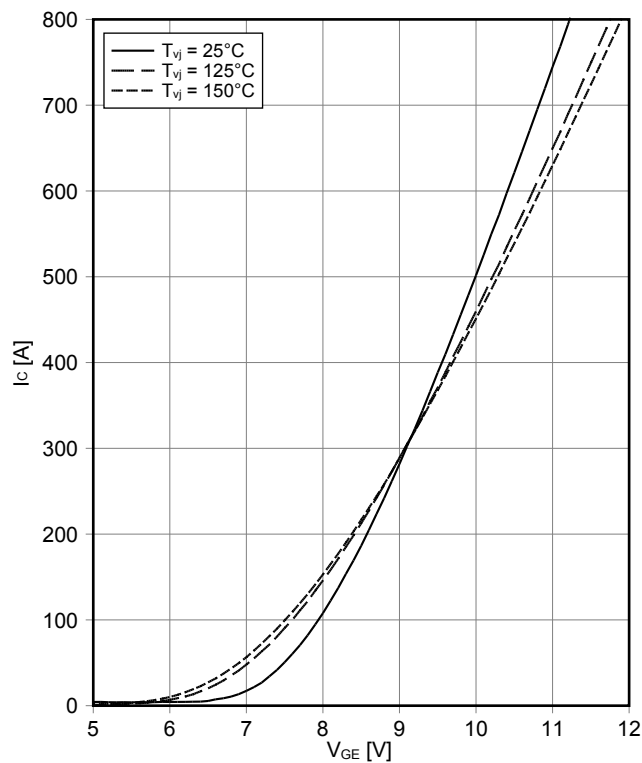
$I_C = f(V_{CE})$   
 $T_{vj} = 150^\circ\text{C}$



传输特性 IGBT, 逆变器 (典型)

transfer characteristic IGBT, Inverter (typical)

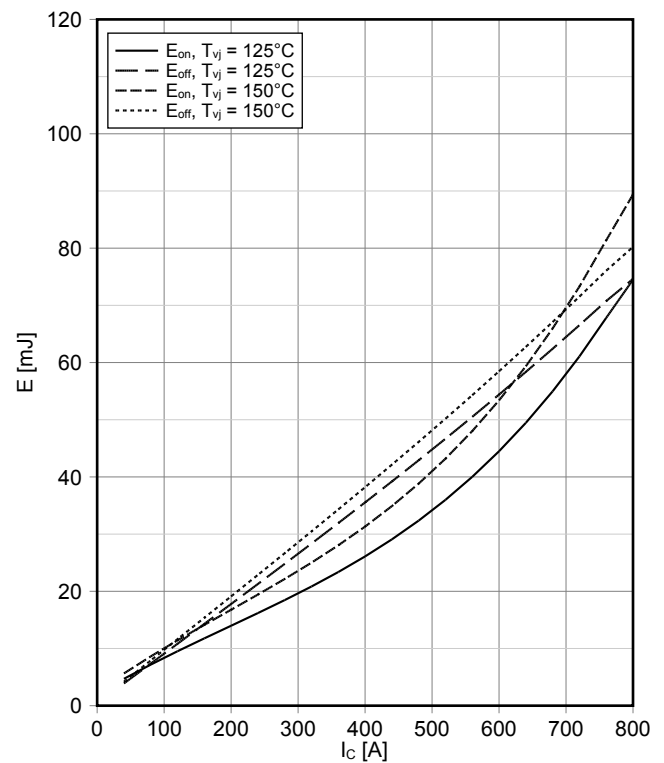
$I_C = f(V_{GE})$   
 $V_{CE} = 20\text{ V}$



开关损耗 IGBT, 逆变器 (典型)

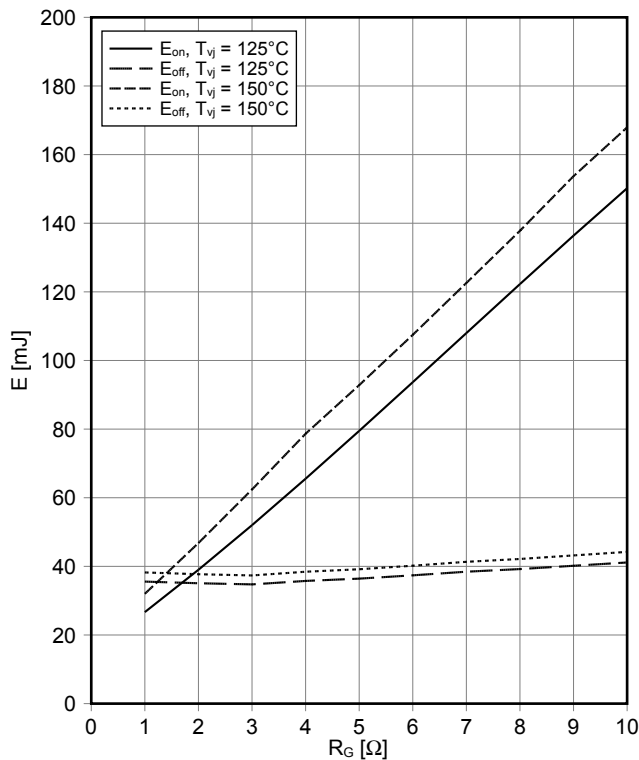
switching losses IGBT, Inverter (typical)

$E_{on} = f(I_C)$ ,  $E_{off} = f(I_C)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Gon} = 1\ \Omega$ ,  $R_{Goff} = 1\ \Omega$ ,  $V_{CE} = 600\text{ V}$

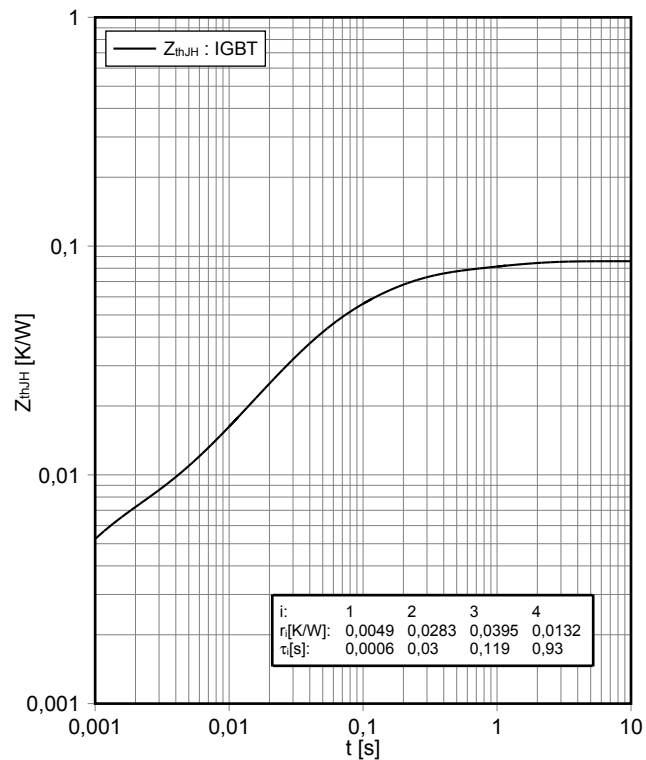


开关损耗 IGBT, 逆变器 (典型)  
**switching losses IGBT, Inverter (typical)**

$E_{on} = f(R_G)$ ,  $E_{off} = f(R_G)$   
 $V_{GE} = \pm 15\text{ V}$ ,  $I_C = 400\text{ A}$ ,  $V_{CE} = 600\text{ V}$

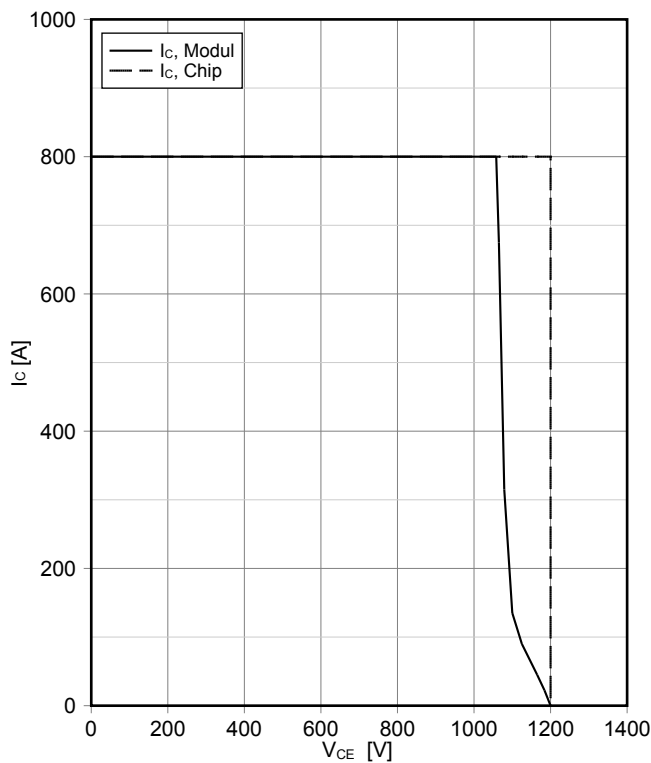


瞬态热阻抗 IGBT, 逆变器  
**transient thermal impedance IGBT, Inverter**  
 $Z_{thJH} = f(t)$

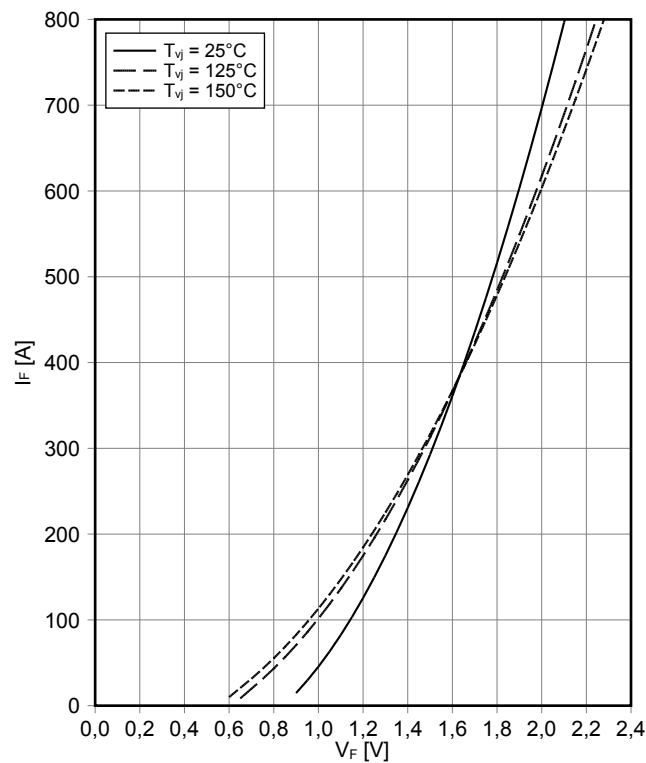


反偏安全工作区 IGBT, 逆变器 (RBSOA)  
**reverse bias safe operating area IGBT, Inverter (RBSOA)**

$I_C = f(V_{CE})$   
 $V_{GE} = \pm 15\text{ V}$ ,  $R_{Goff} = 1\ \Omega$ ,  $T_{vj} = 150^\circ\text{C}$

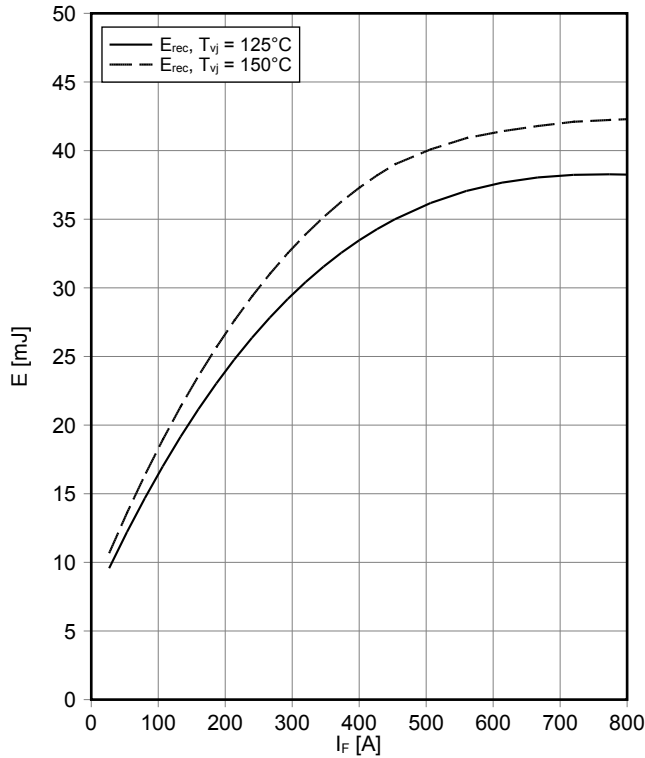


正向偏压特性 二极管, 逆变器 (典型)  
**forward characteristic of Diode, Inverter (typical)**  
 $I_F = f(V_F)$



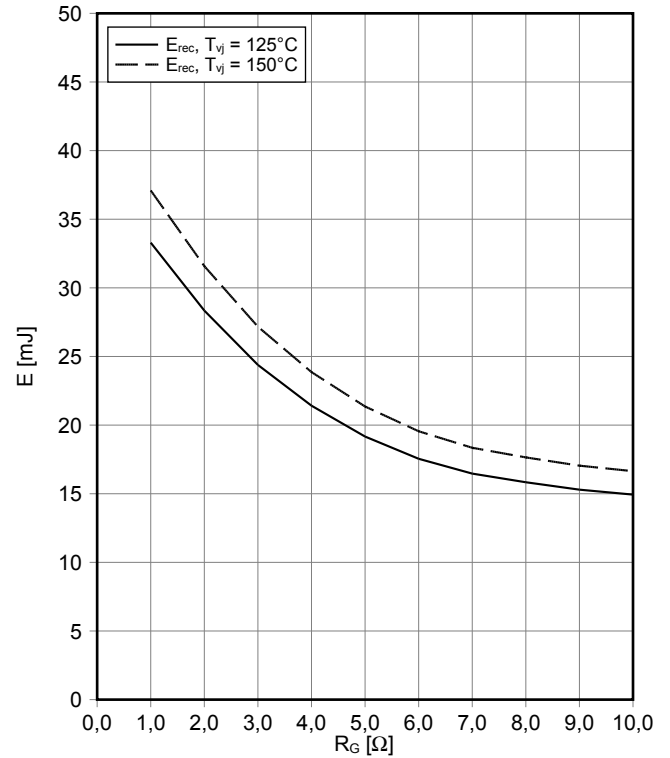
开关损耗 二极管,逆变器 (典型)  
**switching losses Diode, Inverter (typical)**

$E_{rec} = f(I_F)$   
 $R_{Gon} = 1 \Omega, V_{CE} = 600 V$



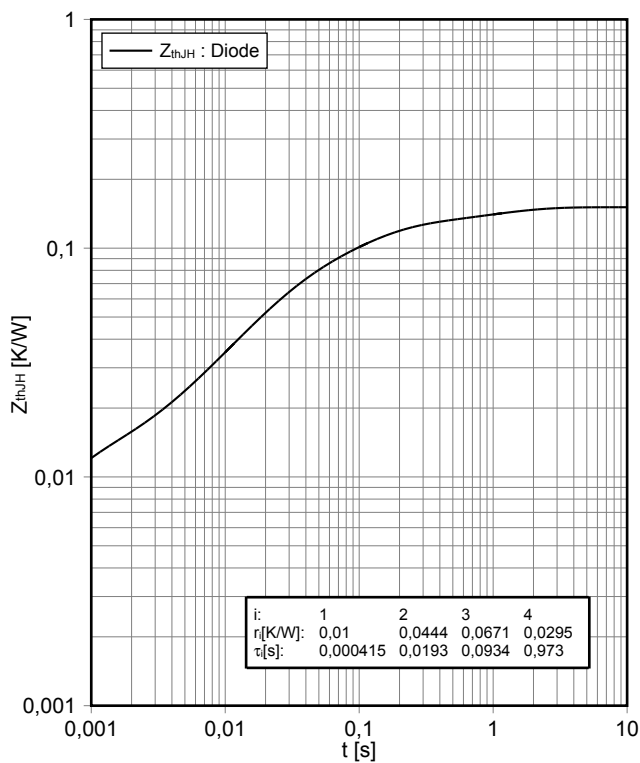
开关损耗 二极管,逆变器 (典型)  
**switching losses Diode, Inverter (typical)**

$E_{rec} = f(R_G)$   
 $I_F = 400 A, V_{CE} = 600 V$

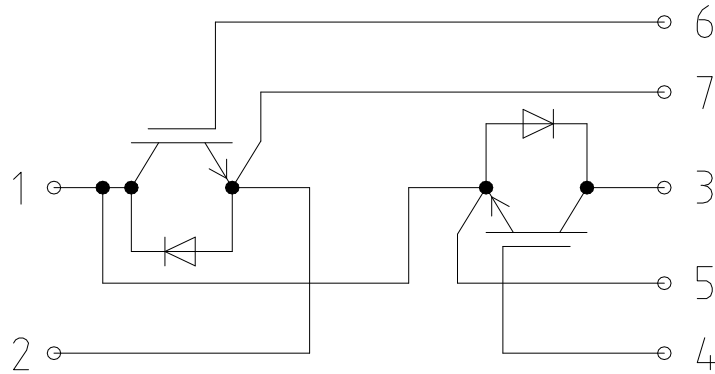


瞬态热阻抗 二极管,逆变器  
**transient thermal impedance Diode, Inverter**

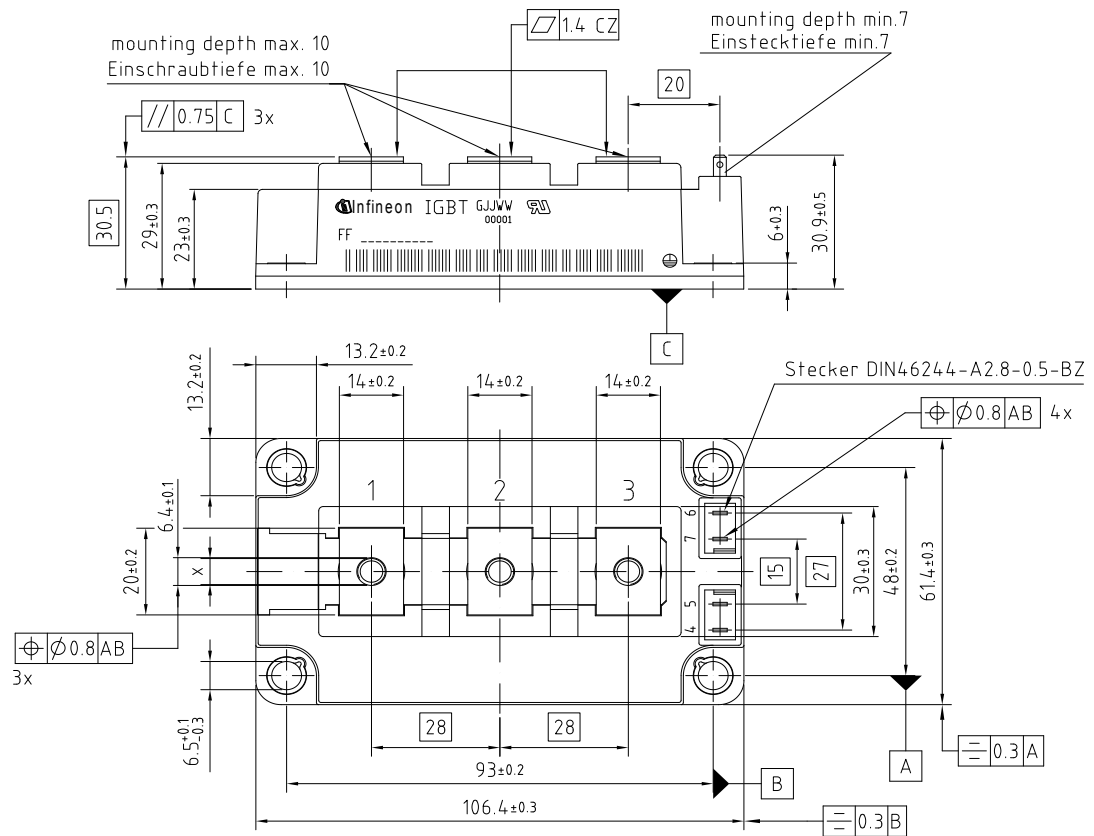
$Z_{thJH} = f(t)$



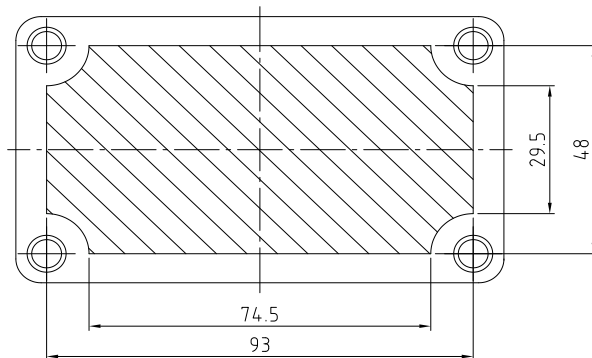
## 接线图 / Circuit diagram



## 封装尺寸 / Package outlines



x: M5/M6 depending on type  
x: M5/M6 je nach Typ



Sperrfläche für Thermisches Interface Material  
restricted area for Thermal Interface Material

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